

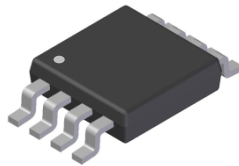
Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max T _A = +25°C
-30V	12mΩ @ V _{GS} = -10V	-10.5A
	21mΩ @ V _{GS} = -4.5V	-8.0A

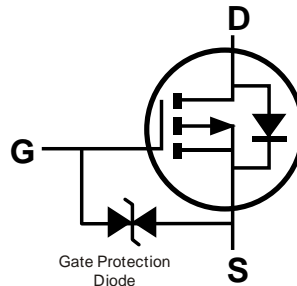
Description and Applications

This MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

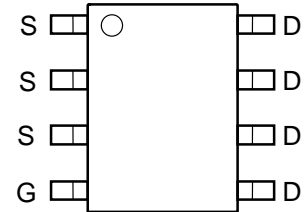
- Backlighting
- Power Management Functions
- DC-DC Converters



Top View



Internal Schematic



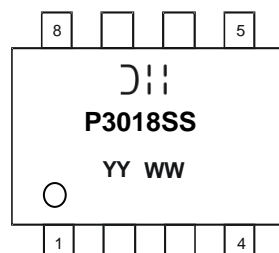
Top View
Pin Configuration

Ordering Information (Note 4)

Part Number	Case	Packaging
DMP3018SSS-13	SO-8	2,500/Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
 2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

Marking Information



- ⌋⌋⌋ = Manufacturer's Marking
- P3018SS = Product Type Marking Code
- YYWW = Date Code Marking
- YY or YY = Year (ex: 18 = 2018)
- WW = Week (01 to 53)

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V _{DSS}	-30	V
Gate-Source Voltage			V _{GSS}	±25	V
Continuous Drain Current (Note 6) V _{GS} = -10V	Steady State	T _A = +25°C	I _D	-10.5	A
		T _A = +70°C		-8.5	
Continuous Drain Current (Note 6) V _{GS} = -10V	Steady State	T _C = +25°C	I _D	-25	A
		T _C = +70°C		-20	
Maximum Continuous Body Diode Forward Current (Note 6)			I _S	-20	A
Pulsed Drain Current (10μs Pulse, Duty Cycle = 1%)			I _{DM}	-90	A
Avalanche Current (Note 7) L = 1mH			I _{AS}	-14	A
Avalanche Energy (Note 7) L = 1mH			E _{AS}	104	mJ

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	T _A = +25°C	P _D	1.2	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	R _{θJA}	101	°C/W
Total Power Dissipation (Note 6)	T _A = +25°C	P _D	1.7	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	R _{θJA}	73	°C/W
Total Power Dissipation (Note 6)		P _D	10	W
Thermal Resistance, Junction to Case (Note 6)		R _{θJC}	12.5	°C/W
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Drain-Source Breakdown Voltage	BV _{DSS}	-30	—	—	V	V _{GS} = 0V, I _D = -250μA
Zero Gate Voltage Drain Current	I _{DSS}	—	—	-1	μA	V _{DS} = -24V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±10	μA	V _{GS} = ±20V, V _{DS} = 0V
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	V _{GS(TH)}	-1.0	—	-3.0	V	V _{DS} = V _{GS} , I _D = -250μA
Static Drain-Source On-Resistance	R _{DS(ON)}	—	8.7	12	mΩ	V _{GS} = -10V, I _D = -11.5A
		—	14.5	21		V _{GS} = -4.5V, I _D = -8.5A
Diode Forward Voltage	V _{SD}	—	-0.7	-1.2	V	V _{GS} = 0V, I _S = -1A
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	C _{iss}	—	2714	—	pF	V _{DS} = -15V, V _{GS} = 0V, f = 1.0MHz
Output Capacitance	C _{oss}	—	727	—	pF	
Reverse Transfer Capacitance	C _{rss}	—	342	—	pF	
Gate Resistance	R _g	—	14.2	—	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1.0MHz
Total Gate Charge (V _{GS} = -5V)	Q _g	—	31	—	nC	V _{DS} = -15V, I _D = -11.5A
Total Gate Charge (V _{GS} = -10V)	Q _g	—	57	—	nC	
Gate-Source Charge	Q _{gs}	—	7	—	nC	
Gate-Drain Charge	Q _{gd}	—	15.5	—	nC	
Turn-On Delay Time	t _{D(ON)}	—	7.8	—	ns	V _{DD} = -15V, V _{GS} = -10V, R _G = 6Ω, I _D = -11.5A
Turn-On Rise Time	t _R	—	17.8	—	ns	
Turn-Off Delay Time	t _{D(OFF)}	—	62.2	—	ns	
Turn-Off Fall Time	t _F	—	40.9	—	ns	
Reverse Recovery Time	t _{RR}	—	21	—	ns	I _S = -11.5A, dI/dt = 100A/μs
Reverse Recovery Charge	Q _{RR}	—	10.5	—	nC	

- Notes:
- Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
 - Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1-inch square copper plate.
 - I_{AS} and E_{AS} ratings are based on low frequency and duty cycles to keep T_J = +25°C.
 - Short duration pulse test used to minimize self-heating effect.
 - Guaranteed by design. Not subject to product testing.

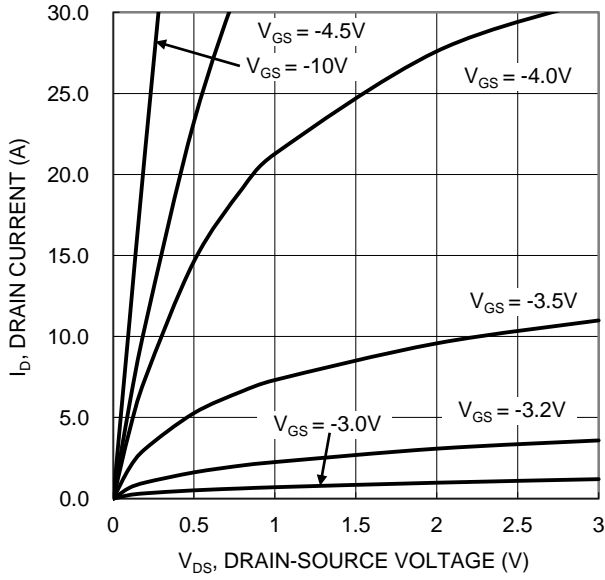


Figure 1. Typical Output Characteristic

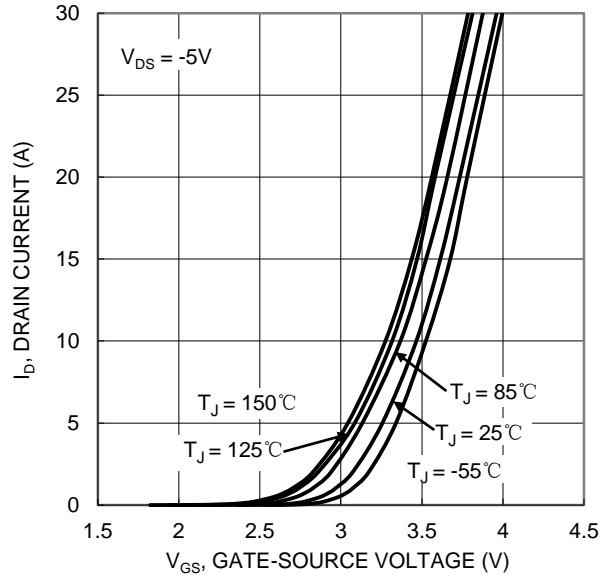


Figure 2. Typical Transfer Characteristic

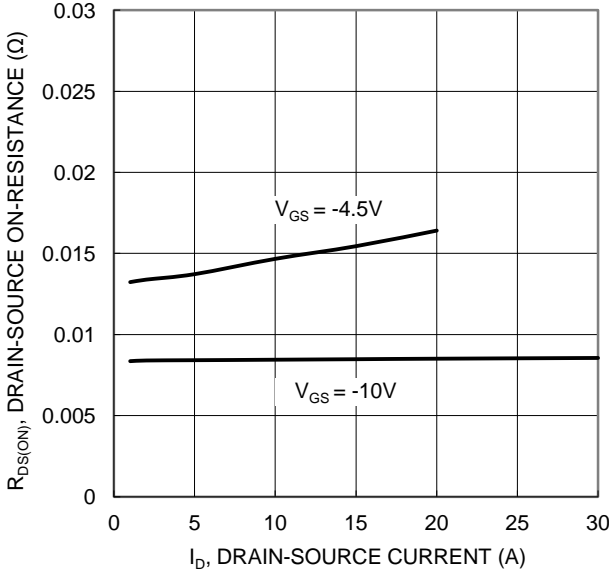


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

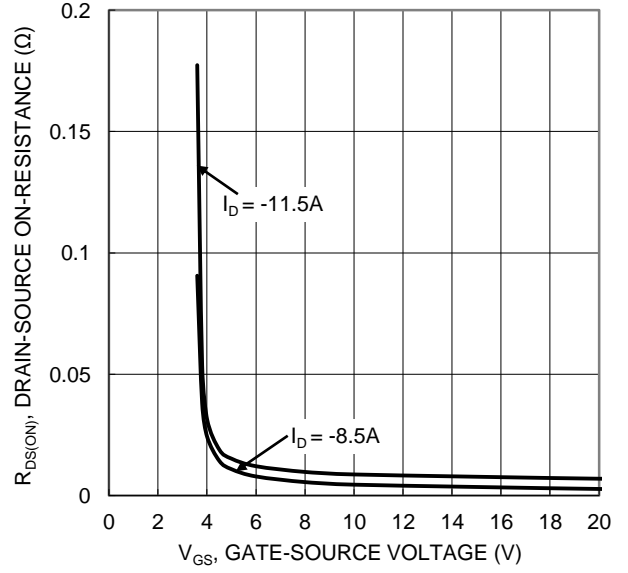


Figure 4. Typical Transfer Characteristic

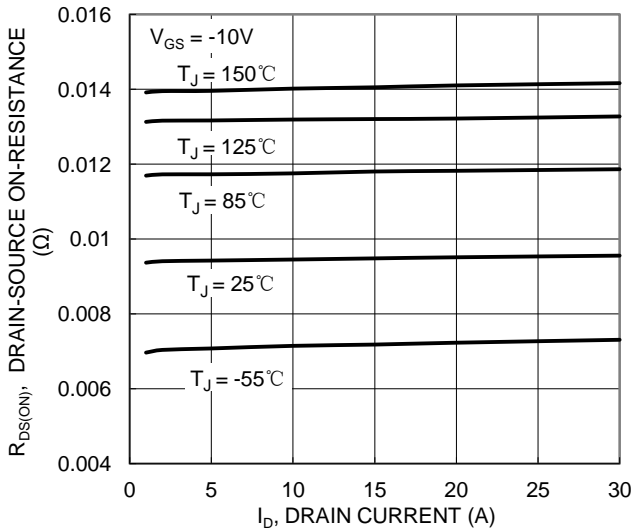


Figure 5. Typical On-Resistance vs. Drain Current and Junction Temperature

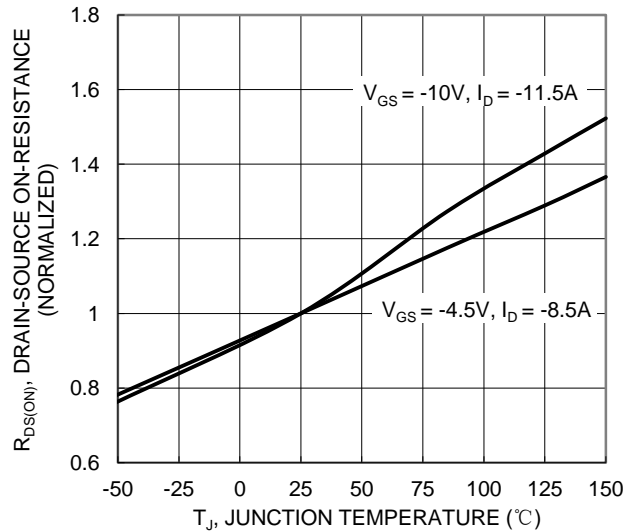


Figure 6. On-Resistance Variation with Junction Temperature

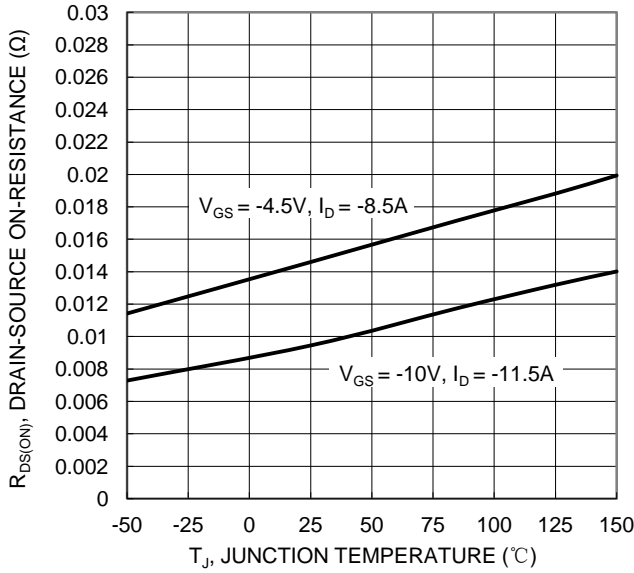


Figure 7. On-Resistance Variation with Junction Temperature

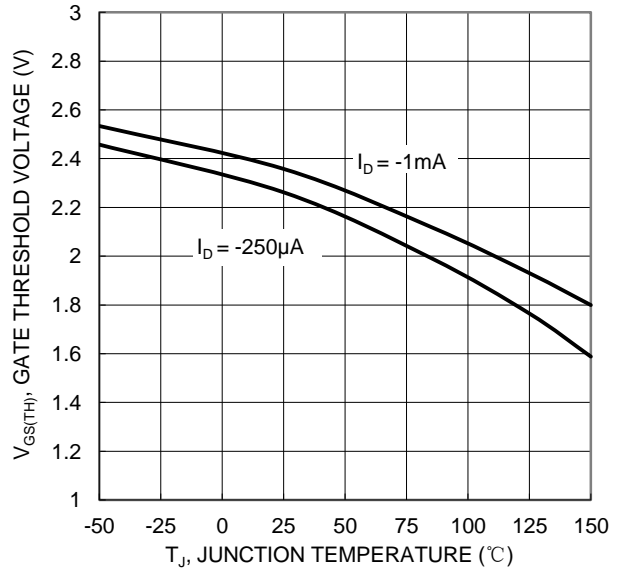


Figure 8. Gate Threshold Voltage vs. Junction Temperature

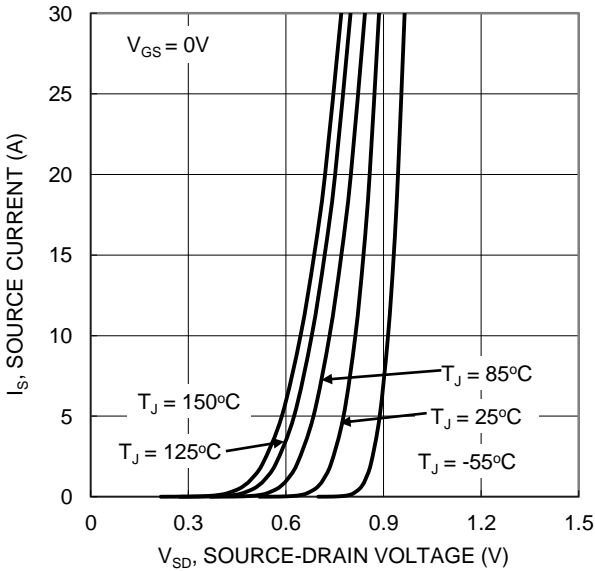


Figure 9. Diode Forward Voltage vs. Current

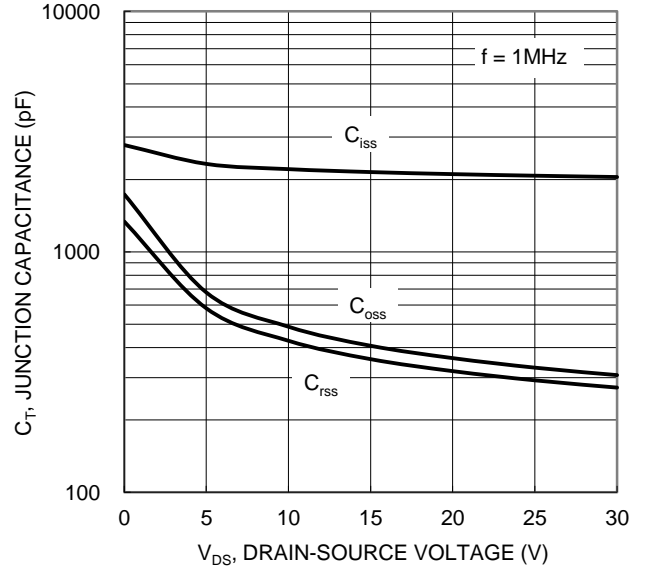


Figure 10. Typical Junction Capacitance

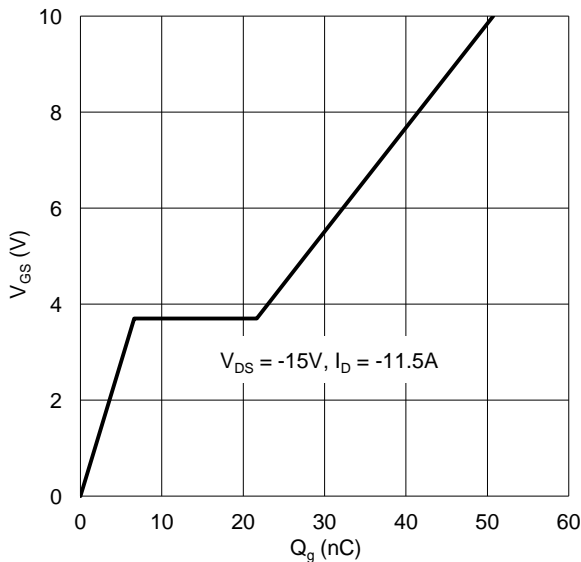


Figure 11. Gate Charge

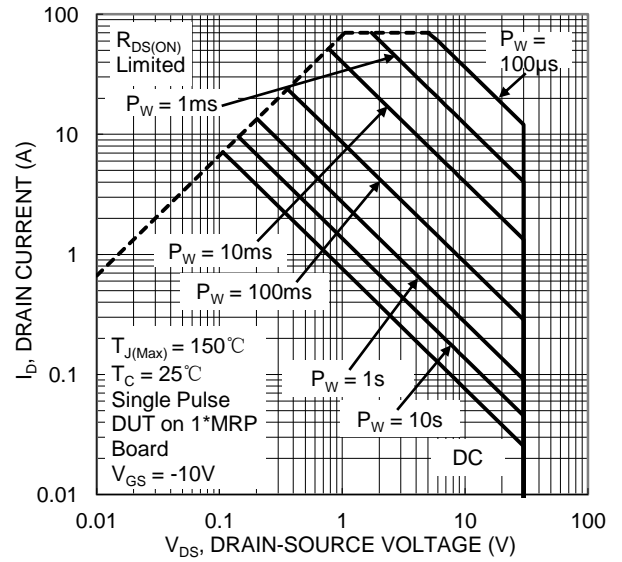


Figure 12. SOA, Safe Operation Area

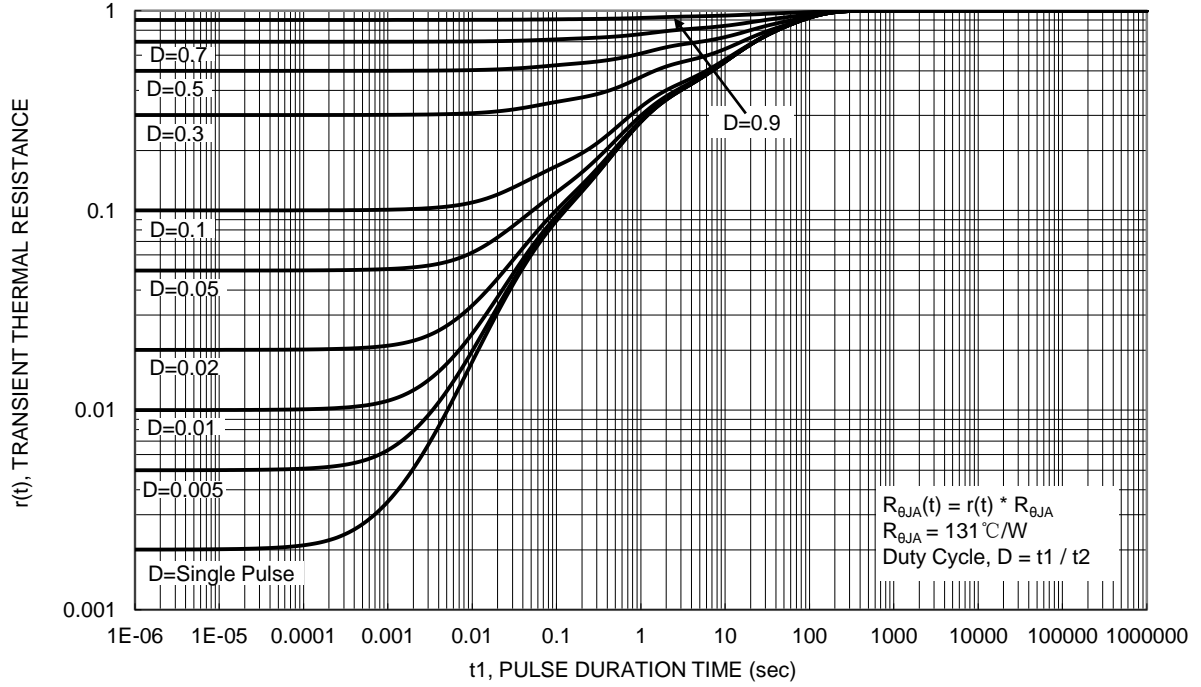
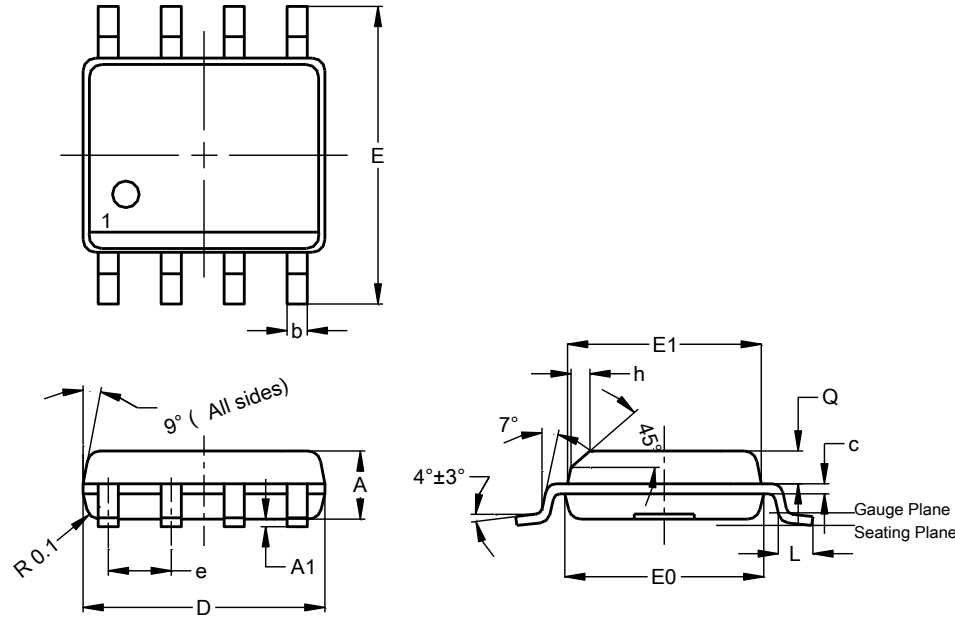


Figure 13. Transient Thermal Resistance

Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SO-8



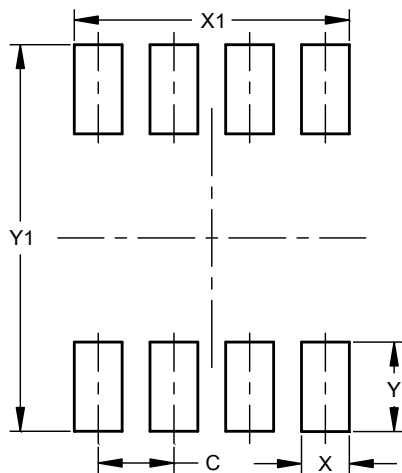
SO-8			
Dim	Min	Max	Typ
A	1.40	1.50	1.45
A1	0.10	0.20	0.15
b	0.30	0.50	0.40
c	0.15	0.25	0.20
D	4.85	4.95	4.90
E	5.90	6.10	6.00
E1	3.80	3.90	3.85
E0	3.85	3.95	3.90
e	--	--	1.27
h	-	--	0.35
L	0.62	0.82	0.72
Q	0.60	0.70	0.65

All Dimensions in mm

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SO-8



Dimensions	Value (in mm)
C	1.27
X	0.802
X1	4.612
Y	1.505
Y1	6.50

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